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(54) Title: INTEGRATION OF DRY DEVELOPMENT AND ETCH PROCESSES FOR EUV PATTERNING IN A SINGLE PROCESS CHAMBER

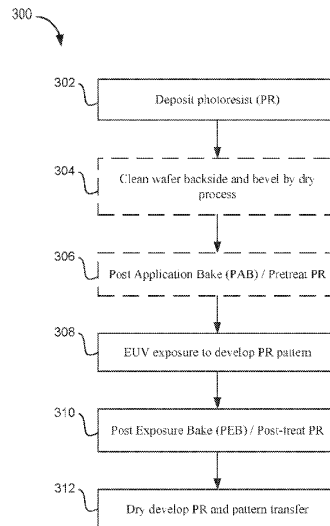


FIG. 3

(57) Abstract: Process condition management facilitates the combination of dry development and etching into a single process chamber; eliminating the necessity for a post-dry development bake step during semiconductor manufacturing. Methods and apparatuses for rapidly instituting a large drop in process chamber pressure allow thermal dry development and an O₂ flash treatment or thermal dry development and plasma hardmask open operations to take place without wafer transfer.

[Continued on next page]

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